



$$h. \quad B = \frac{\hbar}{4\pi c I} \propto \frac{1}{I} \quad I = \sum_i m_j x_i^2$$

$m_j$  larger  $\rightarrow I$  larger  $\rightarrow B$  smaller.

Energy levels get closer :

For center atom  $x_i = 0 \rightarrow$  no effect of atomic mass change.

$$i. \quad |\langle \psi |^2 = 1 \Rightarrow |C|^2 \int (6\phi_A^* + 8\phi_B^*)(6\phi_A + 8\phi_B) dV$$

$$|C|^2 \{ 36|\phi_A|^2 + 64|\phi_B|^2 + 96 \int \phi_A \phi_B dV \}$$

overlap integral  $S'$

$$\Rightarrow |C|^2 \{ 100 + 96S' \} = 1.$$

$$\Rightarrow C = \sqrt{\frac{1}{100 + 96S'}}$$

$$\psi_N = \frac{3\phi_A + 4\phi_B}{\sqrt{25 + 24S'}}$$

$$j. \quad P(\phi_A) = |\langle \phi_A | \psi_N \rangle|^2 = \frac{9}{25 + 24S'}$$

$$P(\phi_B) = \frac{16}{25 + 24S'}$$

imbalance  $\frac{7}{25 + 24S'}$ .

k. polar electric dipole moment

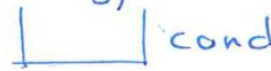
$\Leftrightarrow$  because of the charge imbalance.

$$l. \quad \text{bonding} \quad 6\phi_A + 8\phi_B = \psi$$

$$\text{antibonding} \quad 8\phi_A - 6\phi_B = \psi^*$$

$$\Rightarrow \underline{\underline{\psi^* \psi = 0}}$$

- 2a) use of periodic boundary conditions assumes no direct physical effects due to the boundaries.
- b) lattice vibration
- c) system with a band gap; pure no impurities at  $T=0$  valence shell filled, conduction band empty, at  $T>0$  small fraction of electrons in cond. band. and holes in valence band.
- d) acceptor impurity, accepts "easily" electrons from valence band. Energy level close to top of the valence band.

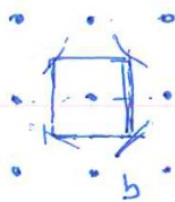


$\Rightarrow$  many holes in valence band  
 $\Rightarrow$  conducts via hole mobility



- e) contact between a donor (n type) and acceptor (p type) semiconductor. In boundary region depletion (recombination) of majority carriers (electrons or holes).  $\Rightarrow$  space-charge region made up by the fixed impurity ions.

- f) square lattice side  $b$



Wigner Seitz cell direct lattice  
 $A_{ws} = b \times b = b^2$

Brillouin zone cell, reciprocal lattice,

$\downarrow$   
 square with spacing  $\frac{2\pi}{b}$ .

$$\Rightarrow A_{BZ} = \frac{4\pi^2}{b^2}$$

- g). Boundaries  $\psi(0) = \psi(L) = 0$ . for  $x$  and  $y$ .

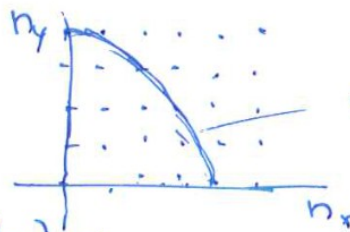
$$S.E. \quad \frac{-\hbar^2}{2m} \left\{ \frac{\partial^2 \psi}{\partial x^2} + \frac{\partial^2 \psi}{\partial y^2} \right\} + \underbrace{V}_{=0} = E \psi.$$

$$\frac{+\hbar^2}{2m} \left\{ \frac{\pi^2}{L^2} n_x^2 \psi + \frac{\pi^2}{L^2} n_y^2 \psi \right\} = \text{Const } \psi$$

$$h) \quad E = \frac{+\hbar^2 \pi^2}{2mL^2} (n_x^2 + n_y^2) = \frac{+\hbar^2 \pi^2}{2mL^2} n^2$$

- i)  $n_x$  and  $n_y$  characterize a orbital which accommodates 2 states (spin up and spin down).

$$n_x, n_y \geq 0$$



$$n_F = \cancel{n} \cdot n_{\max}$$

⇒ number of orbitals:

$$\frac{1}{4} \pi n_F^2$$

$$\Rightarrow \frac{N}{2} = \frac{1}{4} \pi n_F^2 \Rightarrow n_F^2 = \frac{2N}{\pi}$$

$$\Rightarrow E_F = \frac{\hbar^2 \pi^2 N}{mL^2}$$

j.  $\frac{N}{L^2} = 10^{12} \text{ cm}^{-2}$

$$E_F = \frac{\pi (1.05)^2 \cdot 10^{-68} \cdot 10^{16}}{9.11 \times 10^{-31}} = \frac{\pi (1.05)^2}{9.11} \times 10^{-21} \left[ \frac{\text{J}^2}{\text{kg m}^2} \right] = [\text{J}]$$

$$1 \text{ J} = 1.6 \times 10^{-19} \text{ eV} \rightarrow E_F = 2.4 \text{ meV}$$

k. from (i).  $N = \frac{mL^2}{\hbar^2 \pi} E$

$$D(E) = \frac{\partial N}{\partial E} = \frac{mL^2}{\hbar^2 \pi}$$

l.  $b \rightarrow b/2$ .  $E_F$  does not depend on lattice distance.  
number of electrons increases by a factor of 2  $\rightarrow N \rightarrow 2N$ .

$$\Rightarrow E_F \Rightarrow 2E_F$$

m. No influence if  $d < \lambda_F$  as  $\lambda_F$  is the shortest relevant wavelength.

$$\lambda_F = \frac{2\pi}{k_F}, \quad k_F = \frac{\pi}{L} n_F = \frac{1}{L} \sqrt{2\pi N}$$

$$\text{So } \lambda_F = L \sqrt{\frac{2\pi}{N}}$$

$$\text{So, 2D-like if } d < L \sqrt{\frac{2\pi}{N}}$$